

# isc Silicon PNP Power Transistor

## **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -40V(Min.)
- · Good Linearity of hFE
- Complement to Type 2SC2530
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

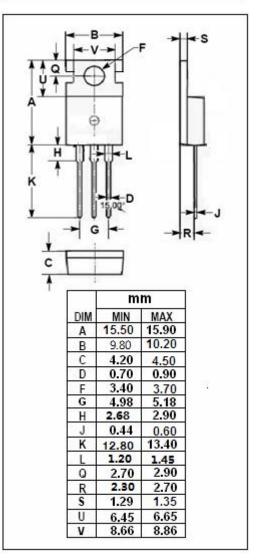
# PIN 1. BASE 2.COLLECTOR 3. BMITTER 1 2 3 TO-220C package

### **APPLICATIONS**

• Designed for medium power amplifier applications.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-40	V
Vceo	Collector-Emitter Voltage	-40	V
V <sub>EBO</sub>	Emitter-Base Voltage	-7	V
Ic	Collector Current-Continuous	-0.5	А
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	20	W
TJ	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	age Temperature Range -65~150	





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2SA1080

### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; R <sub>BE</sub> = ∞	-40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I <sub>C</sub> = -0.1 μ A; I <sub>E</sub> = 0	-40			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -0.1 μ A; I <sub>C</sub> = 0	-7			V
$V_{\text{CE(sat)}}$	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = -1mA			-0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = -1mA			-1.0	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> = 0			-100	nA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -40V; I <sub>B</sub> = 0			-500	nA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -7V; I <sub>C</sub> = 0			-100	nA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -10mA; V <sub>CE</sub> = -5V	100		350	
Сов	Outut Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -20V; f= 1.0MHz		65		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -10mA;V <sub>CE</sub> = -10V; f=10MHz		30		MHz

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